ABSTRACT

TITLE OF INVENTION: COMPOUND FOR FORMING METAL-CONTAINING FILM, COMPOSITION FOR FORMING METAL-CONTAINING FILM, AND PATTERNING PROCESS

The present invention is a compound for forming a metal-containing film to be contained in a composition for forming a metal-containing film, including: at least one metal atom selected from the group consisting of Ti, Zr, and Hf; and a ligand coordinated to the metal atom, wherein the ligand contains a ligand represented by the following general formula (1). The present invention can provide: a compound for forming a metal-containing film having better dry etching resistance than conventional resist underlayer film materials and also having high filling and planarizing properties at the same time; a composition for forming a metal-containing film using the compound; and a patterning process using the composition.

$$HO—X—R^{A1} \qquad (1)$$

[Fig. 1(A)- 1(F)]